

Notice of References Cited

Application/Control No.

09/625,178

Applicant(s)/Patent Under
Reexamination
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Examiner

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Art Unit

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-			
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	K	US-			
	L	US-			
	M	US-			

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	N	JP-04-253372	09-1992	Japan	Yamaguchi	H01L 27/118
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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